

#### **Features**

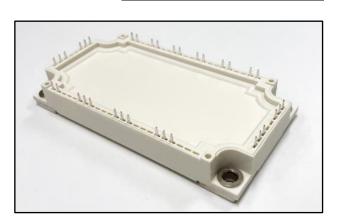
- Low V<sub>CE(sat)</sub>
- Fast Switching
- High Ruggedness
- Short-Circuit Rated



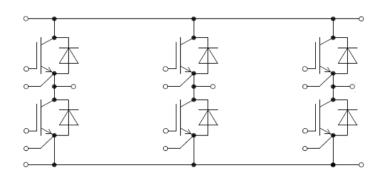
Product Summary				
V <sub>CES</sub>	1200V			
Ic	200A			
V <sub>CE(sat),typ</sub>	1.6V			

### **Applications**

- General Purpose Inverters
- Frequency Converters
- Industrial Motor Drives
- Uninterruptible Power Supply (UPS)
- Servos



#### **Internal Connection**





### IGBT, Inverter

### **Absolute Maximum Ratings**

Parameter	Symbol	Limit	Unit	
Collector-to-Emitter Voltage	V <sub>CES</sub> 1200			
Gate-to-Emitter Voltage	V	±20	V	
Transient Gate-emitter Voltage ( $t_p \le 10 \mu s$ , D < 0.010)	V <sub>GES</sub>	±30		
Continuous DC Collector Current (T <sub>c</sub> = 100°C, T <sub>J</sub> = 175°C)	I <sub>CDC</sub>	200		
Repetitive Peak Collector Current (t <sub>p</sub> = 1ms)	I <sub>CRM</sub>	400	A	
Maximum Power Dissipation (T <sub>c</sub> = 25°C, T <sub>J</sub> = 175°C)	P <sub>D(max)</sub>	1042	W	



### Electrical Characteristics (1), (2)

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Collector-to-Emitter Breakdown Voltage	BV <sub>CES</sub>	V <sub>GE</sub> = 0V, I <sub>C</sub> = 250μA	1200	-	-	V	
Collector-to-Emitter Leakage Current	I <sub>CES</sub>	V <sub>CE</sub> = 1200V, V <sub>GE</sub> = 0V	-	-	5	mA	
Gate-to-Emitter Leakage Current	I <sub>GES</sub>	V <sub>CE</sub> = 0V, V <sub>GE</sub> = ±20V	-	-	400	nA	
Gate Threshold Voltage	V <sub>GE(th)</sub>	$V_{CE} = V_{GE}$ , $I_C = 8mA$	5.0	6.5	7.5		
		V <sub>GE</sub> = 15V, I <sub>C</sub> = 200A	-	1.6	2.0		
		V <sub>GE</sub> = 15V, I <sub>C</sub> = 200A,		2.15		V	
Collector-to-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	T <sub>J</sub> = 150°C	-	2.15	-		
		$V_{GE} = 15V, I_{C} = 200A,$ $T_{J} = 175^{\circ}C$	-	2.25	-		
Total Gate Charge	Qg	$V_{CC} = 600V,$ $V_{GE} = \pm 15V,$ $I_{C} = 200A$	-	2.2	-	μC	
Internal Gate Resistance	R <sub>Gint</sub>	-	-	2.4	-	Ω	
Input Capacitance	C <sub>iss</sub>	V <sub>CE</sub> = 25V,	-	15.4	-		
Output Capacitance	C <sub>oss</sub>	V <sub>GE</sub> = 0V,	-	0.73	-	nF	
Reverse Transfer Capacitance	C <sub>rss</sub>	f = 1MHz	-	0.15	-		
Turn-on Delay time	t <sub>d(ON)</sub>		-	374	-	ns mJ	
Rise Time	t <sub>r</sub>	V <sub>CC</sub> = 600V,	-	82	-		
Turn-off Delay time	t <sub>d(OFF)</sub>	$V_{GE} = \pm 15V,$ $R_G = 1\Omega,$	-	387	-		
Fall Time	t <sub>f</sub>	I <sub>C</sub> =200A, L <sub>load</sub> = 0.3mH,	-	83	-		
Turn-On Switching Loss	E <sub>on</sub>	Energy losses include "tail" and diode reverse	-	13	-		
Turn-Off Switching Loss	E <sub>off</sub>	recovery.	-	13.9	-		
IGBT Total Switching Loss	E <sub>ts</sub>		-	26.9	-		
Turn-on Delay time	t <sub>d(ON)</sub>		-	396	-		
Rise Time	t <sub>r</sub>	$V_{CC} = 600V,$ $V_{GE} = \pm 15V,$	-	93	-	nc	
Turn-off Delay time	t <sub>d(OFF)</sub>	$R_G = 1\Omega$ , $I_C = 200A$ ,	-	486	-	ns	
Fall Time	t <sub>f</sub>	$L_{load} = 0.3 mH$ ,	-	139	-		
Turn-On Switching Loss	Eon	Energy losses include "tail" and diode reverse	-	28.5	-		
Turn-Off Switching Loss	E <sub>off</sub>	recovery. T <sub>J</sub> = 150°C	-	21.9	-	mJ	
IGBT Total Switching Loss	E <sub>ts</sub>	1, 200 0	-	50.4	-		
Short Circuit Collector Current	I <sub>C(SC)</sub>	$V_{GE}$ = 15V, $V_{CC} \le 600V$ , $t_{SC} \le 10\mu s$	-	850	-	А	



# • Diode, Inverter

### **Absolute Maximum Ratings**

Parameter	Symbol	Limit	Unit
Repetitive Peak Reverse Voltage	$V_{RRM}$	1200	V
Continuous DC Forward Current	I <sub>F</sub>	200	^
Repetitive Peak Forward Current	I <sub>FRM</sub>	400	А

#### **Electrical Characteristics (1)**

Parameter	Symbol Test Conditions		Min	Тур	Max	Unit	
Diode Forward Voltage		I <sub>F</sub> = 200A	-	1.65	2.0		
	V <sub>F</sub>	I <sub>F</sub> = 200A T <sub>J</sub> = 150°C	-	1.95	-	V	
		I <sub>F</sub> = 200A T <sub>J</sub> = 175°C	_ 2.0 _				
Diode Reverse-Recovery Charge	$Q_{rr}$		-	19.5	-	μC	
Diode Peak Reverse-Recovery Current	I <sub>rrm</sub>	V <sub>R</sub> = 600V, I <sub>F</sub> = 200A, dI <sub>F</sub> /dt = -1850A/μs	-	89	=	А	
Diode Reverse-Recovery Loss	E <sub>rr</sub>	,,	-	8.35	-	mJ	

# • NTC thermistors

#### Characteristics

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Rated Resistance	R <sub>25</sub>		-	5.0	-	kΩ
Deviation of R100	ΔR/R	$T_{C} = 100^{\circ}C$ $R_{100} = 493.3\Omega$	-5	-	5	%
Power Dissipation	P <sub>25</sub>		-	-	20.0	mW
B-value	B <sub>25/50</sub>	$R_2 = R_{25} \exp [B_{25/50}(1/T_2 - 1/(298.15 K))]$	-	3375	-	К

# • Module

#### **Absolute Maximum Ratings**

Parameter	Symbol		Unit
Maximum Junction Temperature	Tj	-40 to +175	
Operating Junction Temperature	T <sub>vj op</sub>	-40 to +150	°C
Storage Temperature	T <sub>stg</sub>	-40 to +125	
Isolation Voltage ( f = 50Hz, t = 1min)	V <sub>ISO</sub>	2.5	kV



#### **Characteristics**

Parameter	Symbol	Min	Тур	Max	Unit
Material of Module Baseplate	-	-	Cu	-	-
Internal Isolation	-	-	Al <sub>2</sub> O <sub>3</sub>	-	-
Creepage Distance, Terminal to Terminal	-	-	10	-	mm
Clearance, Terminal to Terminal	-	-	7.5	-	mm
Stray Inductance, Module	L <sub>SCE</sub>	-	21	-	nH
Module Lead Resistance, Terminal to Chip	R <sub>CC'+EE'</sub>	-	1.8	-	mΩ
Junction-to-Case Thermal Resistance, per IGBT, Inverter	В	-	0.12	-	°C /\\
Junction-to-Case Thermal Resistance, per Diode, Inverter	- R <sub>θJC</sub>	-	0.19	-	°C/W
Case-to-Heatsink Thermal Resistance, per IGBT, Inverter		-	0.09	-	
Case-to-Heatsink Thermal Resistance, per Diode, Inverter	$R_{\theta CH}$	-	0.16	-	°C/W
Case-to-Heatsink Thermal Resistance, per Module		-	0.01	-	
Mounting Torque for Module Mounting, Screw M5	М	3.0	-	6.0	Nm
Weight per Module	G	-	300	-	g

<sup>(1)</sup>  $T_J = 25$ °C unless otherwise specified

(2)  $t_{r}\!\!:$  from 10% of Ic to 90% of Ic;  $t_{f}\!\!:$  from 90% of Ic to 10% of Ic;

 $E_{on} :$  from 10% of  $V_{GE}$  to 10% of  $V_{CE}; \quad E_{off} :$  from 90% of  $V_{GE}$  to 10% of Ic.



# • Typical Electrical Characteristics

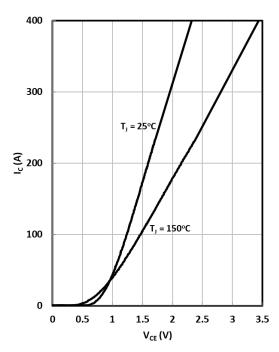


Fig. 1 IGBT (Inverter) Output Characteristics

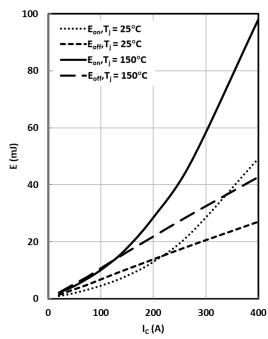


Fig. 3 IGBT (Inverter) Switching Loss vs.Ic  $(V_{CC}=600V,\,V_{GE}=\pm15V,\,R_G=1\Omega)$ 

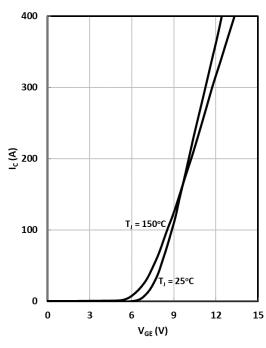


Fig. 2 IGBT (Inverter) Transfer Characteristics

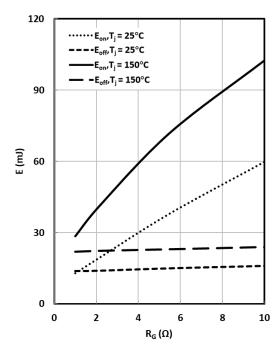


Fig. 4 IGBT (Inverter) Switching Loss vs.R<sub>G</sub> ( $V_{CC} = 600V$ ,  $V_{GE} = \pm 15V$ ,  $I_C = 200A$ )



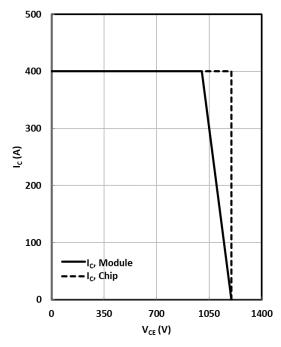


Fig. 5 RBSOA

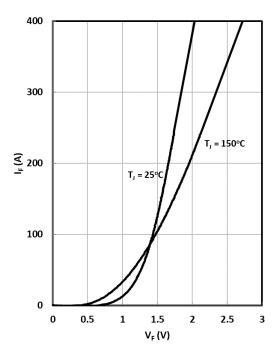


Fig. 6 Diode (Inverter) Forward Characteristics

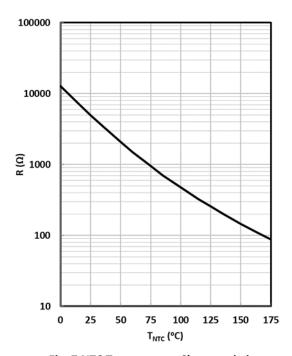
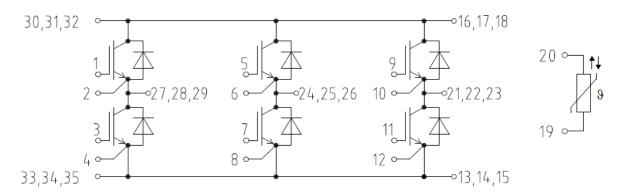


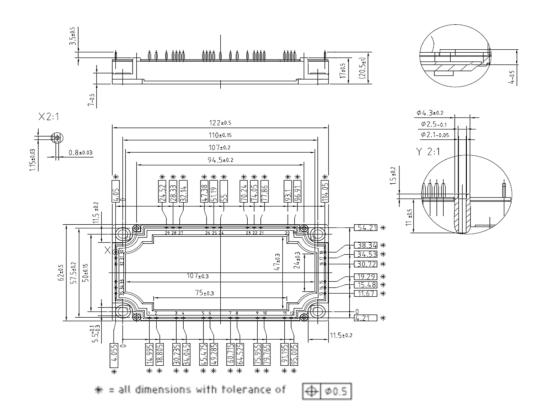
Fig. 7 NTC Temperature Characteristics



# • Circuit diagram



# Package Dimensions





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